NSN 5961-01-381-8983

Diode Semiconductor Device - Page 1 of 1

View Online at https://aerobasegroup.com/nsn/5961-01-381-8983

Inclosure Material:

Ceramic

Overall Length:

Between 2.92 millimeters and 3.81 millimeters

Overall Height:

Between 1.50 millimeters and 2.41 millimeters

Overall Width:

Between 1.50 millimeters and 2.41 millimeters

Mounting Method:

Press fit

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

70.0 breakdown voltage, dc

Current Rating Per Characteristic:

1.00 microamperes forward current, average peak

Power Rating Per Characteristic:

500.0 milliwatts small-signal input power, common-collector absolute

Capacitance Rating In Picofarads:

1.1

Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius ambient air

Test Data Document:

80063-a3132209 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

2 case

Shelf Life:

N/a

Unit Of Measure:

--

Demilitarization:

No

Fiig:

A110a0